

Silicon Schottky Barrier Diode

HRW0302A

■ Features

- Low forward voltage drop and suitable for high efficiency rectifying.
- MPAK package is suitable for high density surface mounting and high speed assembly.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	20	V
Average rectified current	I_o	300	mA
Non-repetitive peak forward surge current	I_{FSM} (Note 1)	3	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to + 125	$^\circ\text{C}$

Note

1. 10msec sine wave 1 pulse

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F = 200\text{ mA}$			0.40	V
Reverse current	I_R	$V_R = 20\text{ V}$			100	$\mu\text{ A}$
Capacitance	C	$V_R = 0\text{ V}, f = 1\text{ MHz}$			100	pF
Thermal resistance	$R_{th(j-a)}$	Polyimide board		340		$^\circ\text{C/W}$

■ Marking

Marking	S11
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